

Low - eld di usion magneto-therm opower of a high m obility tw o-dim ensional electron gas

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(D ated: April 14, 2024)

The low magnetic eld di usion therm opower of a high mobility GaAs-heterostructure has been measured directly on an electrostatically de ned micron-scale Hall-bar structure (4 μm \times 8 μm) at low temperature ($T = 1.6\text{ K}$) in the low magnetic eld regime ($B \leq 1.2\text{ T}$) where delocalized quantum Hall states do not in uence the measurements. The sample design allowed the determination of the eld dependence of the therm opower both parallel and perpendicular to the temperature gradient, denoted respectively by S_{xx} (longitudinal therm opower) and S_{yx} (Nemst-Ettinghausen coe cient). The experimental data show clear oscillations in S_{xx} and S_{yx} due to the formation of Landau levels for $0.3\text{ T} < B \leq 1.2\text{ T}$ and reveal that $S_{yx} \approx 120 S_{xx}$ at a magnetic eld of 1 T, which agrees well with the theoretical prediction that the ratio of these tensor components is dependent on the carrier mobility: $S_{yx}/S_{xx} = 2l_c/l$.

Keywords: Therm oelectric e ect, magnetotransport
PACS Num bers: 72.20.-i, 72.20.Pa, 72.20.Fr

Therm opower experiments have been used extensively to obtain information on transport and scattering in two-dimensional electron gases (2DEGs) in compound semiconductors (for reviews, see Refs. [1] and [2]). Because of the strong electron phonon coupling in these systems, the experimental signal is usually dominated by phonon-drag, hence, apart from the desired electronic transport contributions, the signal also contains a very significant contribution due to details of the electron-phonon interaction. In order to extract the true electronic or "di usion" therm opower, usually drastic approximations have to be made [1, 2]. It would thus be very desirable to have an experimental approach that is not in uenced by phonon-drag effects and directly yields the di usion therm opower. In this paper we describe the development of such an experiment.

We present direct measurements of the magnetic eld dependence of the di usion therm opower using current heating techniques in specially designed micro-Hall bar structures. The samples were fabricated from high mobility GaAs-AlGaAs heterostructures [$\approx 100\text{ m}^2/(\text{Vs})$] using split-gate techniques. A current passing through an electron channel adjoining the Hall structure is used to exclusively heat the electron gas, leaving the lattice temperature unchanged. This current-heating technique has previously been successfully used to determine the di usion therm opower of mesoscopic systems such as quantum point contacts [3] and quantum dots [4, 5, 6]. The present sample design allows the direct measurement of the tensor components of the therm opower both parallel (S_{xx}) and perpendicular (S_{yx}) to the temperature gradient in x-direction. The results are discussed in the framework of theoretical models developed for the mag-

netic eld regime where the formation of Landau levels leads to a modulation of the density of states [7], but does not yet induce the formation of edge states. Therefore, the magnetic eld in the present study is restricted to the low eld regime ($B \leq 1.2\text{ T}$) where the influence of the quantum Hall effect can be neglected.

Fig. 1 shows an SEM -photograph of the sample structure, including a schematic diagram of the measurement. The micro-Hall bar and the electron heating channel are defined by Schottky-gates, thus forming the quantum point contacts (QPCs), which are used as voltage probes. Gates A, D, E and F form the micro-Hall bar and gates A, B, C and D the heating channel. Utilizing the fact that the therm opower of a QPC is quantized [3], QPC₄ and QPC₅ are used to determine the electron temperature in the channel T_{ch} by measuring the voltage drop $V_{25} = V_5 - V_2$ across the electron channel, while gates E and F are not defined. We then have $V_{25} = (S_{\text{QPC}5} - S_{\text{QPC}4}) T_{\text{ch}}$, where T_{ch} equals the temperature difference between the electrons in the channel (T_{ch}) and in the surrounding 2DEG ($T_1 \approx 1.6\text{ K}$), which is in thermal equilibrium with the crystal lattice:

$T_{\text{ch}} = T_{\text{ch}} - T_1$ [8]. Note that the temperature difference T_{ch} enters here rather than a gradient, since the therm ovolage across a QPC can only be measured globally. Experimentally, one observes that $T_{\text{ch}} \propto I^2$, where I is the net heating current, as expected from a simple heat balance equation that is valid for not too large current values [9]. Fig. 2 shows the experimentally determined therm ovolage as a function of the channel heating current. It can be seen that the parabolic dependence is valid for currents up to 12 μA . For the temperature calibration the therm opower of QPC₄ was adjusted

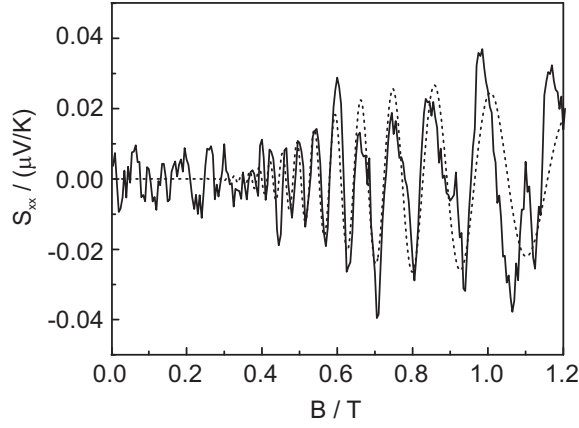


FIG. 3: Thermopower S_{xx} parallel to the temperature gradient: The solid line corresponds to the experimental data for $T = 2.5$ K and the dashed dotted line represents the calculation according to Eq. 3.

Hall structure.

For both components, the experiments show clear oscillations in the thermopower with magnetic field (Figs. 3 and 4). The thermopower signal has been calculated from the thermovoltage measurement assuming the linear temperature gradient as mentioned above. The presented field range studied can be separated into two parts: First, $B < 0.3$ T; the electrons are considered as classical particles which are deflected by the applied magnetic field and scattered elastically at the device boundaries (mean free path $l_{mfp} \approx 8$ nm) [10], and second, $0.3 < B < 1.2$ T where the oscillations correspond to the formation of Landau levels in the 2DEG and hence to the magnetic field dependent modulation of the density of states. In the following, we will present a detailed quantitative discussion of the second magnetic field regime ($0.3 < B < 1.2$ T).

According to Ref. [7] the magnetic field behaviour of the thermopower oscillations can, in the regime of Landau level formation, be described by the following equations:

$$S_{xx} = \frac{2}{1 + \frac{1}{2} \frac{k_B}{e} T_D} \frac{k_B}{e} D^0(X) \exp \left[\frac{2^2 k_B T_D}{h \omega_c} \sin \frac{2\pi f}{B} \right] \quad (1)$$

$$S_{yx} = \frac{4 \omega_c}{1 + \frac{1}{2} \frac{k_B}{e} T_D} \frac{k_B}{e} D^0(X) \exp \left[\frac{2^2 k_B T_D}{h \omega_c} \sin \frac{2\pi f}{B} \right] \quad (2)$$

where T_D is the Dingle temperature, ω_c the cyclotron frequency, τ the transport relaxation time, and f is the frequency of the oscillations ($f = B = E_F = h \omega_c$, where E_F

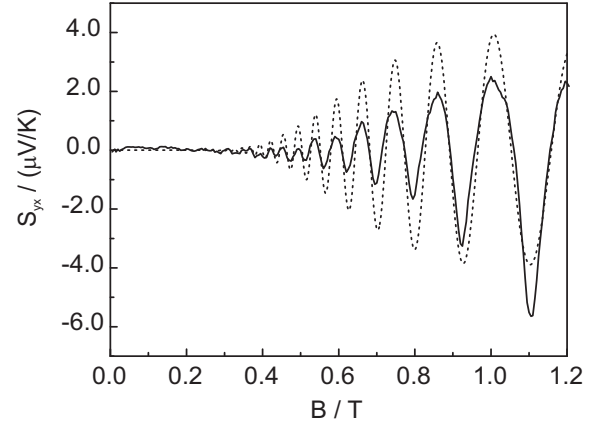


FIG. 4: Thermopower S_{yx} perpendicular to the temperature gradient: The solid line corresponds to the experimental data for $T = 2.5$ K and the dashed dotted line represents the calculation according to Eq. 4.

is the Fermi energy). The quantity $D^0(X)$ is the derivative of the thermal damping factor $D(X)$, defined by $D(X) = X / \sinh X$ where $X = \frac{1}{2} \frac{k_B T}{h \omega_c}$. These equations were originally [7] derived for conditions where $\omega_c < 1$, which would restrict the validity in our case to magnetic fields up to $B \approx 20$ mT. However, Coleridge et al. [12] have shown that Eqs. (3) and (4) are valid up to much higher field values ($B \approx 1$ T) when localization effects can be neglected (as it is the case for high mobility 2DEGs).

The results of the measurements up to 1.2 T are presented in Fig. 3 and Fig. 4 together with fits using Eqs. (1) and (2). For the fits, the carrier density n and the mobility μ were taken from the transport characterization. The Dingle temperature was obtained from the assumption that the quantum mobility is approximately 10 times lower than the electron mobility i.e. $T_D = 10 \times 0.4$ K [7, 12]. The thermal smearing was fitted by a free parameter \overline{T}_e , which can be interpreted as the average electron temperature in the micro-Hall bar. The best fits for an average electron temperature of $\overline{T}_e = 4$ K is in very good agreement with the estimates made above concerning the temperature gradient.

Both S_{xx} and S_{yx} can be fitted satisfactorily using the same set of parameters, even though the amplitudes are very different. According to Eqs. (3) and (4), the ratio of the thermopower perpendicular and parallel to the temperature gradient is given by $S_{yx}/S_{xx} = 2 \omega_c$. For the present sample, the measured ratio at $B = 1$ T is ≈ 120 . Again, this value agrees well with the expected value of 160. To our knowledge this is the first successful measurement of the diffusion thermopower for a semiconductor 2DEG system. The current heating approach allows us to avoid the influence of phonon-drag effects [7, 14, 15]. From the consistency of the average

temperatures and the temperature gradients, which are obtained from the fitting and the channel temperature calibration, it can be concluded that the chosen geometry and the measurement configuration are suitable for investigating the dissipation thermopower of high mobility samples.

Summarizing, the results presented here demonstrate that electron heating techniques can be used to measure directly the longitudinal and transverse components of the dissipation thermopower. For low magnetic fields, thermopower fluctuations are observed which originate from quasiballistic electrons; for higher fields, the modulation of the electron density of states due to Landau level formation determines the oscillatory part of the dissipation thermopower. Current theories [2, 7] describe this oscillatory behavior to a large extent and can be used to independently gauge the electron temperature. The consistency of these measurements with theory opens up the way for an alternative method for studying the dissipation thermopower in the QHE as well as in the fractional quantum Hall effect regime, where currently, experimental data are discussed controversially [1, 16, 17, 18].

This work performed with financial support from the Deutsche Forschungsgemeinschaft (DFG Mo 771/5-2).

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